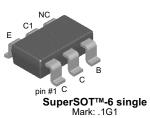


SEMICONDUCTOR®

FMBSA06

NPN General Purpose Amplifier

- This device is designed for general purpose amplifier applications at collector currents to 300 mA.
- Sourced from Process 12.



Absolute Maximum Ratings* T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	80	V
V _{CBO}	Collector-Base Voltage	80	V
√ _{EBO}	Emitter-Base Voltage	4.0	V
С	Collector Current - Continuous	500	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics T_a=25°C unless otherwise noted

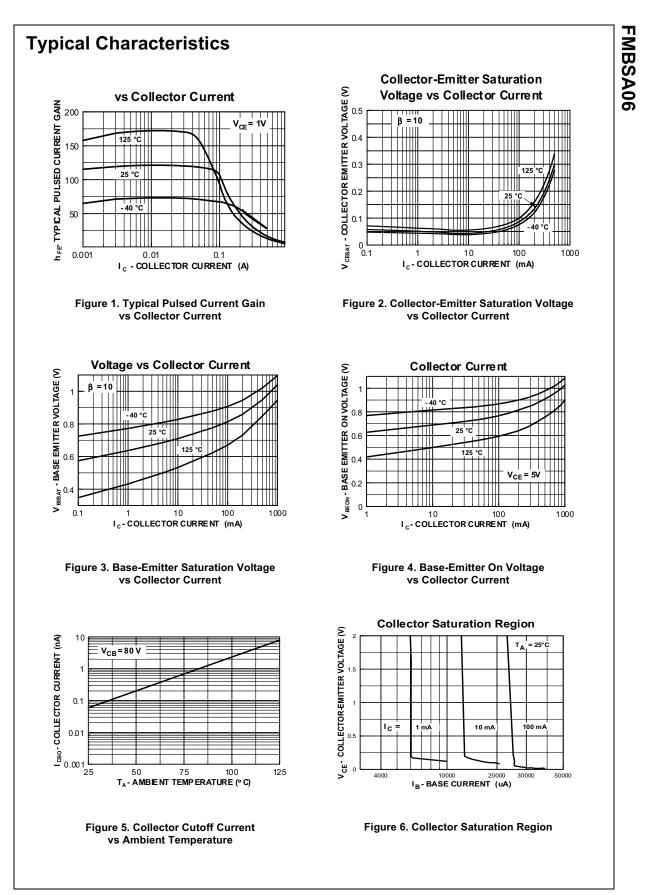
Parameter	Test Condition	Min.	Max.	Units
eristics			•	
Collector-Emitter Sustaining Voltage *	I _C = 1.0mA, I _B = 0	80		V
Emitter-Base Breakdown Voltage	I _E = 100μA, I _C = 0	4.0		V
Collector Cut-off Current	$V_{CE} = 60V, I_B = 0$		0.1	μA
Collector Cut-off Current	V _{CB} = 80V, I _E = 0		0.1	μA
eristics				
DC Current Gain	I _C = 10mA, V _{CE} = 1.0V	100		
	I _C = 100mA, V _{CE} = 1.0V	100		
Collector-Emitter Saturation Voltage	I _C = 100mA, I _B = 10mA		0.25	V
Base-Emitter On Voltage	I _C = 10mA, V _{CE} = 1.0V		1.2	V
I Characteristics		-		
Current Gain Bandwidth Product	I _C = 10mA, V _{CE} = 2.0V, f = 100MHz	100		MHz
	eristics Collector-Emitter Sustaining Voltage * Emitter-Base Breakdown Voltage Collector Cut-off Current Collector Cut-off Current eristics DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter On Voltage I Characteristics	eristics Collector-Emitter Sustaining Voltage * $I_C = 1.0mA$, $I_B = 0$ Emitter-Base Breakdown Voltage $I_E = 100\muA$, $I_C = 0$ Collector Cut-off Current $V_{CE} = 60V$, $I_B = 0$ Collector Cut-off Current $V_{CB} = 80V$, $I_E = 0$ eristics DC Current Gain $I_C = 10mA$, $V_{CE} = 1.0V$ $I_C = 100mA$, $V_{CE} = 1.0V$ I_C = 100mA, $I_B = 10mA$ Base-Emitter On Voltage $I_C = 10mA$, $V_{CE} = 1.0V$ I Characteristics I	eristics Collector-Emitter Sustaining Voltage * $I_C = 1.0mA$, $I_B = 0$ 80 Emitter-Base Breakdown Voltage $I_E = 100\muA$, $I_C = 0$ 4.0 Collector Cut-off Current $V_{CE} = 60V$, $I_B = 0$ 4.0 Collector Cut-off Current $V_{CB} = 80V$, $I_E = 0$ 9 eristics DC Current Gain $I_C = 10mA$, $V_{CE} = 1.0V$ 100 Collector-Emitter Saturation Voltage $I_C = 100mA$, $V_{CE} = 1.0V$ 100 Collector-Emitter On Voltage $I_C = 100mA$, $V_{CE} = 1.0V$ 100 ICharacteristics ICharacteristics 100	eristicsCollector-Emitter Sustaining Voltage * $I_C = 1.0mA$, $I_B = 0$ 80Emitter-Base Breakdown Voltage $I_E = 100\muA$, $I_C = 0$ 4.0Collector Cut-off Current $V_{CE} = 60V$, $I_B = 0$ 0.1Collector Cut-off Current $V_{CB} = 80V$, $I_E = 0$ 0.1eristicsDC Current Gain $I_C = 10mA$, $V_{CE} = 1.0V$ 100 $I_C = 100mA$, $V_{CE} = 1.0V$ 100 $I_C = 100mA$, $V_{CE} = 1.0V$ 100Base-Emitter Saturation Voltage $I_C = 100mA$, $V_{CE} = 1.0V$ 1.2I Characteristics

Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2.0%

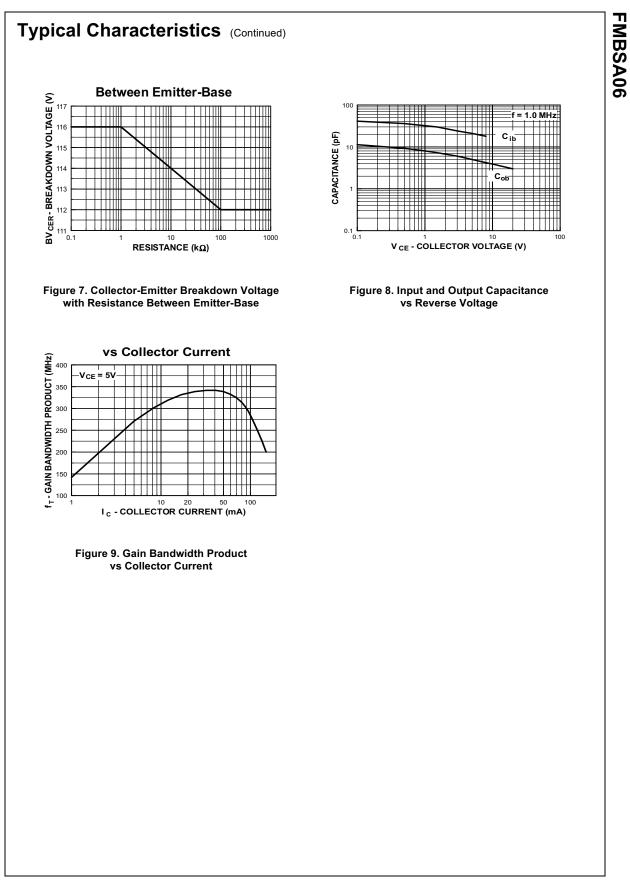
Thermal Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Max.	Units
P _D	Total Device Dissipation *	700	mW
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient, total	180	°C/W

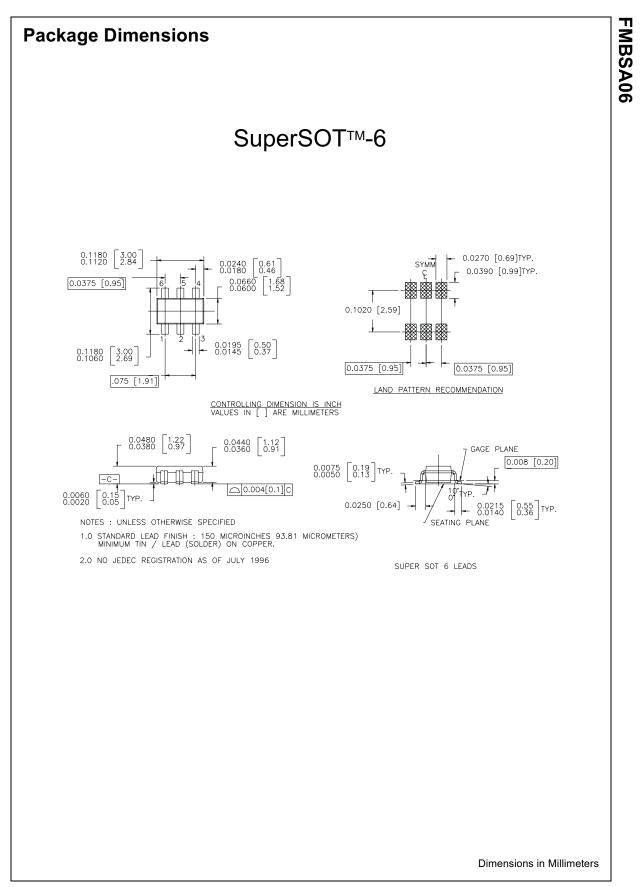
Device mounted on a 1 in 2 pad of 2 oz copper.



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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.